
2SD1366

Silicon NPN Epitaxial

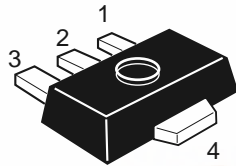
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Application

Low frequency power amplifier

Outline

UPAK



1. Base
2. Collector
3. Emitter
4. Collector (Flange)

2SD1366

Absolute Maximum Ratings (Ta = 25°C)

Item	Symbol	Ratings	Unit
Collector to base voltage	V_{CBO}	25	V
Collector to emitter voltage	V_{CEO}	20	V
Emitter to base voltage	V_{EBO}	5	V
Collector current	I_C	1	A
Collector peak current	$i_{C(peak)}^{*1}$	1.5	A
Collector power dissipation	P_C^{*2}	1	W
Junction temperature	Tj	150	°C
Storage temperature	Tstg	-55 to +150	°C

Notes: 1. PW ≤ 10 ms, Duty cycle ≤ 20%.

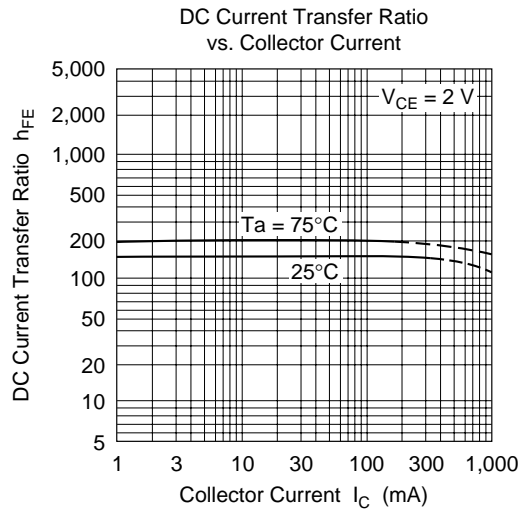
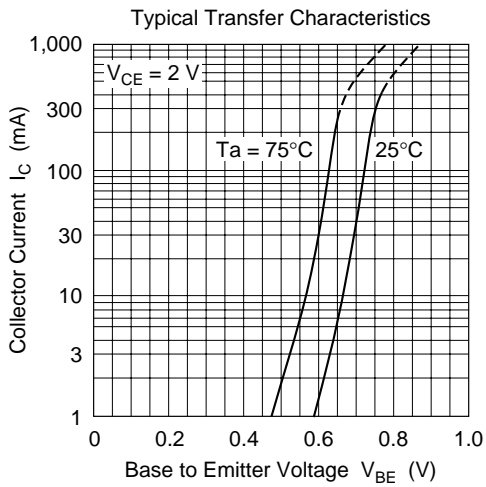
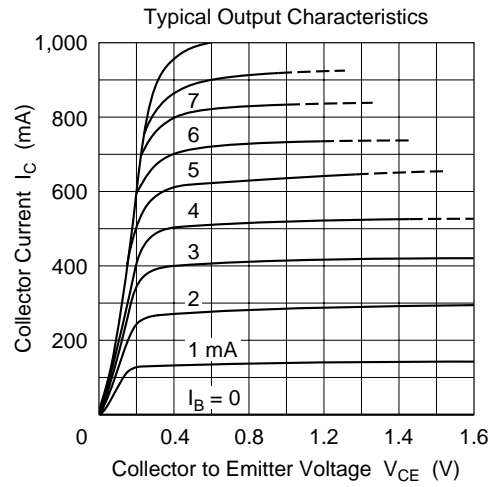
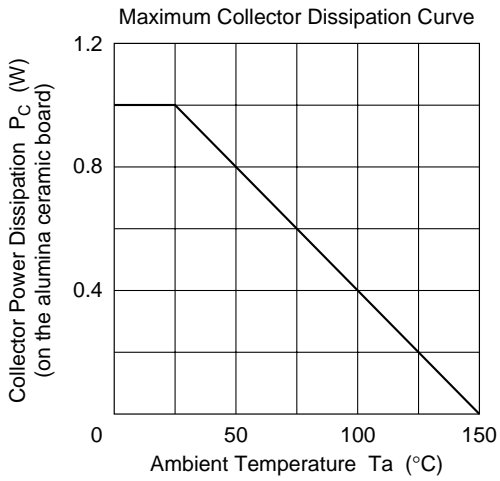
2. Value on the alumina ceramic board (12.5 × 20 × 0.7 mm)

Electrical Characteristics (Ta = 25°C)

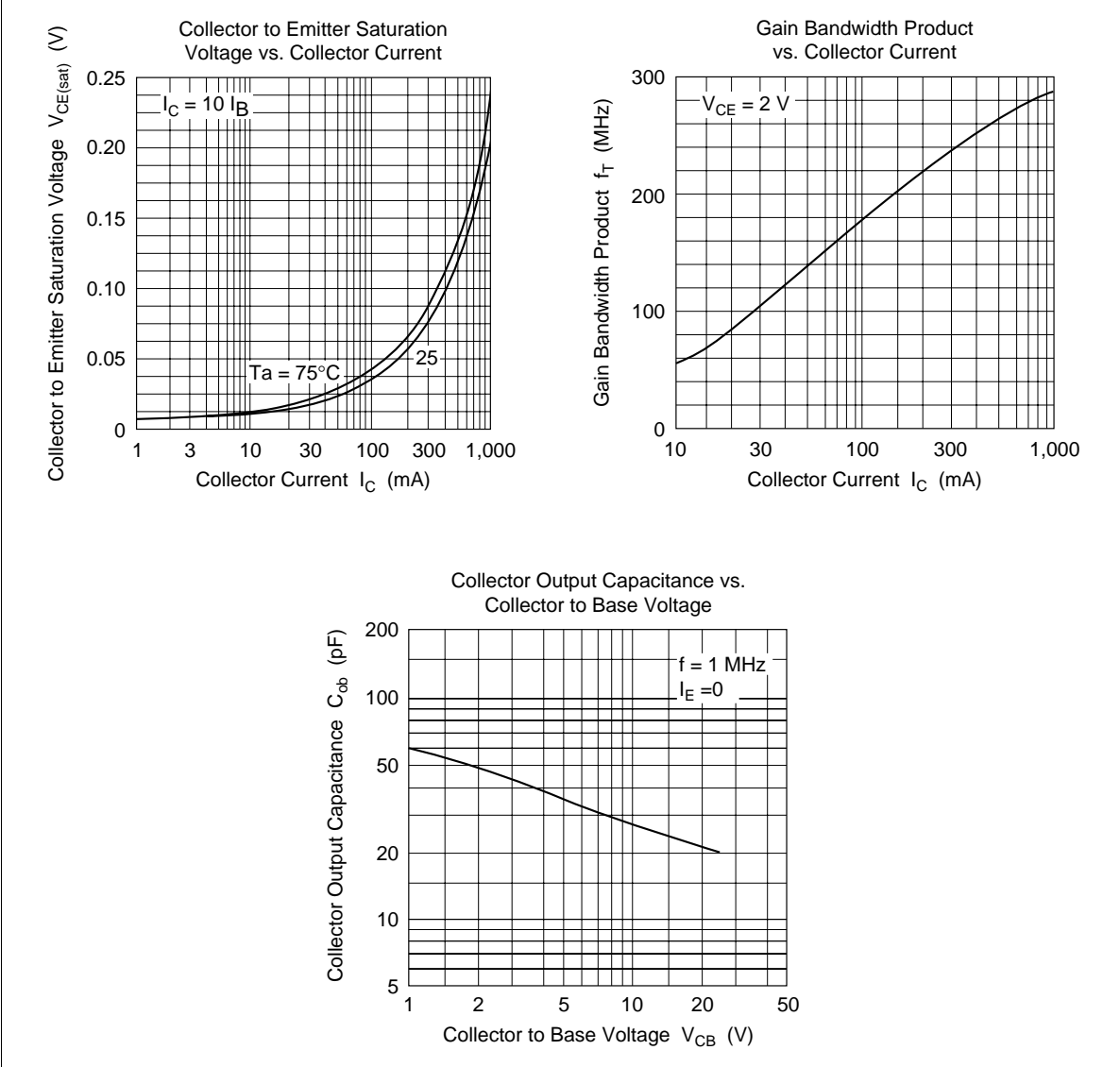
Item	Symbol	Min	Typ	Max	Unit	Test conditions
Collector to base breakdown voltage	$V_{(BR)CBO}$	25	—	—	V	$I_C = 10 \mu A, I_E = 0$
Collector to emitter breakdown voltage	$V_{(BR)CEO}$	20	—	—	V	$I_C = 1 \text{ mA}, R_{BE} = \infty$
Emitter to base breakdown voltage	$V_{(BR)EBO}$	5	—	—	V	$I_E = 10 \mu A, I_C = 0$
Collector cutoff current	I_{CBO}	—	—	0.1	μA	$V_{CB} = 20 \text{ V}, I_E = 0$
Emitter cutoff current	I_{EBO}	—	—	0.1	μA	$V_{EB} = 4 \text{ V}, I_C = 0$
DC current transfer ratio	h_{FE}^{*1}	85	—	240		$V_{CE} = 2 \text{ V}, I_C = 0.5 \text{ A}, \text{ Pulse}$
Collector to emitter saturation voltage	$V_{CE(sat)}$	—	0.15	0.3	V	$I_C = 0.8 \text{ A}, I_B = 0.08 \text{ A}, \text{ Pulse}$
Base to emitter saturation voltage	$V_{BE(sat)}$	—	0.9	1.0	V	$I_C = 0.8 \text{ A}, I_B = 0.08 \text{ A}, \text{ Pulse}$
Gain bandwidth product	f_T	—	240	—	MHz	$V_{CE} = 2 \text{ V}, I_C = 0.5 \text{ A}, \text{ Pulse}$
Collector output capacitance	Cob	—	22	—	pF	$V_{CB} = 10 \text{ V}, I_E = 0, f = 1 \text{ MHz}$

Note: 1. The 2SD1366 is grouped by h_{FE} as follows.

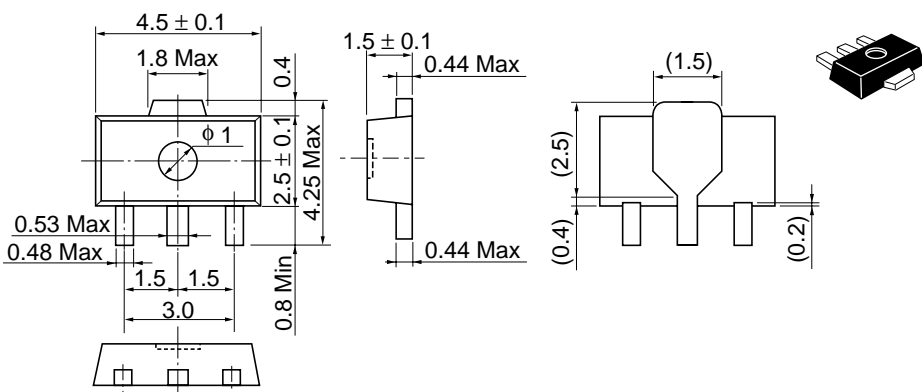
Mark	AA	AB
h_{FE}	85 to 170	120 to 240



2SD1366



Unit: mm



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